

**RADIATION HARDENED  
 POWER MOSFET  
 THRU-HOLE (Low-Ohmic TO-257AA)**

**IRHYB67134CM  
 150V, N-CHANNEL**



**Product Summary**

Part Number	Radiation Level	R <sub>DS(on)</sub>	I <sub>D</sub>
IRHYB67134CM	100K Rads (Si)	0.090Ω	19A
IRHYB63134CM	300K Rads (Si)	0.090Ω	19A



International Rectifier's R6™ technology provides superior power MOSFETs for space applications. These devices have improved immunity to Single Event Effect (SEE) and have been characterized for useful performance with Linear Energy Transfer (LET) up to 90MeV/(mg/cm²). Their combination of very low R<sub>DS(on)</sub> and faster switching times reduces power loss and increases power density in today's high speed switching applications such as DC-DC converters and motor controllers. These devices retain all of the well established advantages of MOSFETs such as voltage control, ease of paralleling and temperature stability of electrical parameters.

**Features:**

- Low R<sub>DS(on)</sub>
- Fast Switching
- Single Event Effect (SEE) Hardened
- Low Total Gate Charge
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Electrically Isolated
- Light Weight

**Absolute Maximum Ratings**

**Pre-Irradiation**

	Parameter		Units
I <sub>D</sub> @ V <sub>GS</sub> = 12V, T <sub>C</sub> = 25°C	Continuous Drain Current	19	A
I <sub>D</sub> @ V <sub>GS</sub> = 12V, T <sub>C</sub> = 100°C	Continuous Drain Current	12	
I <sub>DM</sub>	Pulsed Drain Current ①	76	
P <sub>D</sub> @ T <sub>C</sub> = 25°C	Max. Power Dissipation	75	W
	Linear Derating Factor	0.6	W/°C
V <sub>GS</sub>	Gate-to-Source Voltage	±20	V
EAS	Single Pulse Avalanche Energy ②	67	mJ
I <sub>AR</sub>	Avalanche Current ①	19	A
E <sub>AR</sub>	Repetitive Avalanche Energy ①	7.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	7.8	V/ns
T <sub>J</sub>	Operating Junction	-55 to 150	°C
T <sub>STG</sub>	Storage Temperature Range		
	Lead Temperature	300 (0.063 in. /1.6 mm from case for 10s)	
	Weight	3.7 (Typical)	g

For footnotes refer to the last page

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**Electrical Characteristics @ T<sub>j</sub> = 25°C (Unless Otherwise Specified)**

	Parameter	Min	Typ	Max	Units	Test Conditions
B <sub>V</sub> D <sub>SS</sub>	Drain-to-Source Breakdown Voltage	150	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1.0mA
ΔB <sub>V</sub> D <sub>SS</sub> /ΔT <sub>J</sub>	Temperature Coefficient of Breakdown Voltage	—	0.19	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1.0mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-State Resistance	—	—	0.090	Ω	V <sub>GS</sub> = 12V, I <sub>D</sub> = 12A ④
V <sub>GS(th)</sub>	Gate Threshold Voltage	2.0	—	4.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1.0mA
ΔV <sub>GS(th)</sub> /ΔT <sub>J</sub>	Gate Threshold Voltage Coefficient	—	-9.51	—	mV/°C	
g <sub>fs</sub>	Forward Transconductance	14	—	—	S	V <sub>DS</sub> = 15V, I <sub>DS</sub> = 12A ④
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	—	—	10	μA	V <sub>DS</sub> = 120V, V <sub>GS</sub> = 0V
		—	—	25		V <sub>DS</sub> = 120V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Leakage Forward	—	—	100	nA	V <sub>GS</sub> = 20V
I <sub>GSS</sub>	Gate-to-Source Leakage Reverse	—	—	-100	nA	V <sub>GS</sub> = -20V
Q <sub>g</sub>	Total Gate Charge	—	—	50	nC	V <sub>GS</sub> = 12V, I <sub>D</sub> = 19A
Q <sub>gs</sub>	Gate-to-Source Charge	—	—	15		V <sub>DS</sub> = 75V
Q <sub>gd</sub>	Gate-to-Drain ('Miller') Charge	—	—	18		
t <sub>d(on)</sub>	Turn-On Delay Time	—	—	20	ns	V <sub>DD</sub> = 75V, I <sub>D</sub> = 19A, V <sub>GS</sub> = 12V, R <sub>G</sub> = 7.5Ω
t <sub>r</sub>	Rise Time	—	—	30		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	—	35		
t <sub>f</sub>	Fall Time	—	—	25		
L <sub>S</sub> + L <sub>D</sub>	Total Inductance	—	6.8	—	nH	Measured from Drain lead ( 6mm / 0.025 in from package ) to Source lead ( 6mm/ 0.025 in from package )
C <sub>iss</sub>	Input Capacitance	—	1540	—	pF	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 25V f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	240	—		
C <sub>rss</sub>	Reverse Transfer Capacitance	—	5.2	—		
R <sub>g</sub>	Gate Resistance	—	1.1	—	Ω	f = 1.0MHz, open drain

**Source-Drain Diode Ratings and Characteristics**

	Parameter	Min	Typ	Max	Units	Test Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	19	A	
I <sub>SM</sub>	Pulse Source Current (Body Diode) ①	—	—	76		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.2	V	T <sub>j</sub> = 25°C, I <sub>S</sub> = 19A, V <sub>GS</sub> = 0V ④
t <sub>rr</sub>	Reverse Recovery Time	—	—	300	ns	T <sub>j</sub> = 25°C, I <sub>F</sub> = 19A, di/dt ≤ 100A/μs
Q <sub>RR</sub>	Reverse Recovery Charge	—	—	2.6	μC	V <sub>DD</sub> ≤ 25V ④
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L <sub>S</sub> + L <sub>D</sub> .				

**Thermal Resistance**

	Parameter	Min	Typ	Max	Units	Test Conditions
R <sub>thJC</sub>	Junction-to-Case	—	—	1.67	°C/W	
R <sub>thJA</sub>	Junction-to-Ambient	—	—	80		Typical Socket Mount

Note: Corresponding Spice and Saber models are available on International Rectifier Web site.

For footnotes refer to the last page

## Radiation Characteristics

IRHYB67134CM

International Rectifier Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at International Rectifier is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

**Table 1. Electrical Characteristics @ T<sub>j</sub> = 25°C, Post Total Dose Irradiation** ⑤⑥

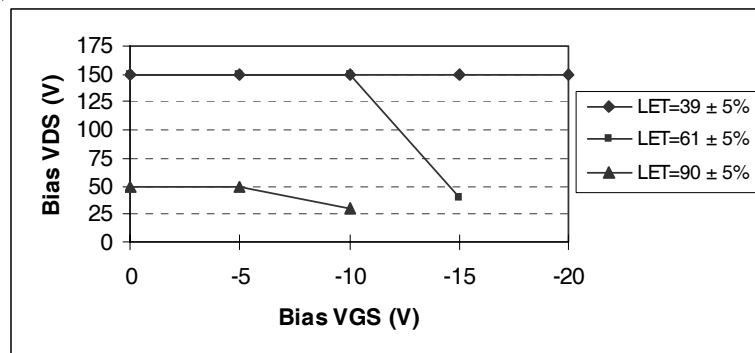
	Parameter	Up to 300K Rads (Si) <sup>1</sup>		Units	Test Conditions
		Min	Max		
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	150	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1.0mA
V <sub>GS(th)</sub>	Gate Threshold Voltage	2.0	4.0		V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 1.0mA
I <sub>GSS</sub>	Gate-to-Source Leakage Forward	—	100	nA	V <sub>GS</sub> = 20V
I <sub>GSS</sub>	Gate-to-Source Leakage Reverse	—	-100		V <sub>GS</sub> = -20V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	—	10	μA	V <sub>DS</sub> = 120V, V <sub>GS</sub> = 0V
R <sub>DS(on)</sub>	Static Drain-to-Source On-State Resistance (TO-3) ④	—	0.092	Ω	V <sub>GS</sub> = 12V, I <sub>D</sub> = 12A
R <sub>DS(on)</sub>	Static Drain-to-Source On-State Resistance (Low Ohmic TO-257) ④	—	0.090	Ω	V <sub>GS</sub> = 12V, I <sub>D</sub> = 12A
V <sub>SD</sub>	Diode Forward Voltage ④	—	1.2	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 19A

1. Part numbers IRHYB67134CM and IRHYB63134CM

International Rectifier radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

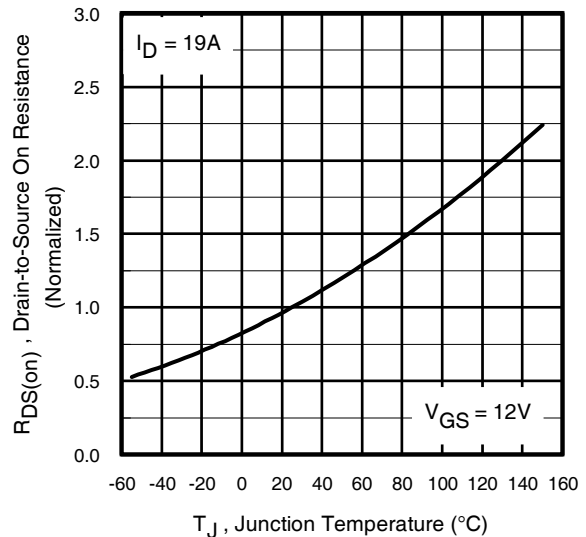
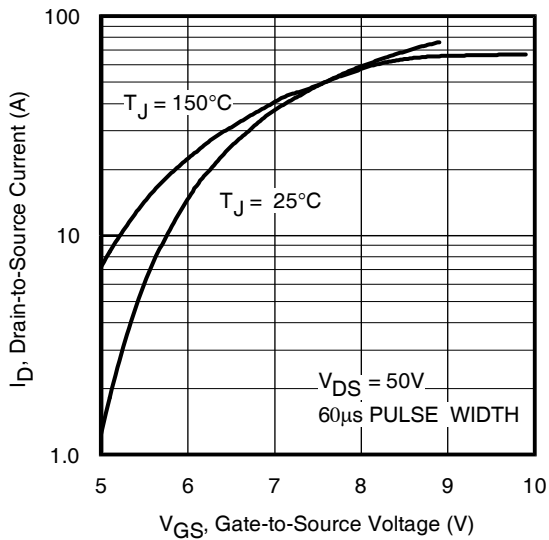
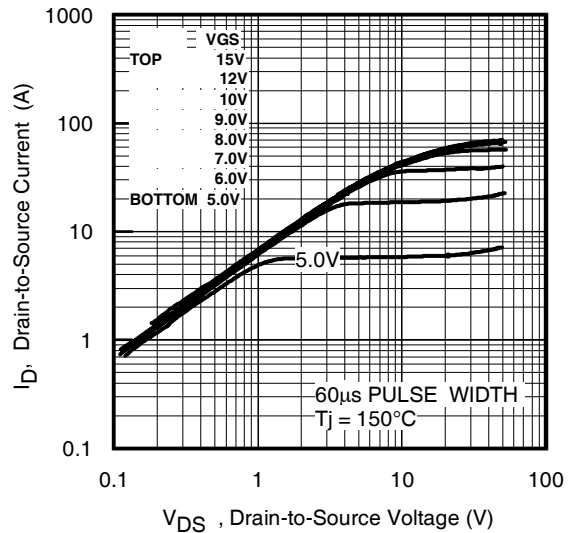
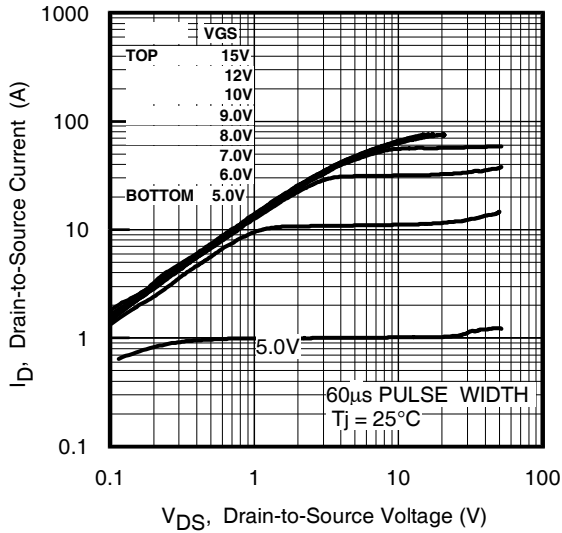
**Table 2. Typical Single Event Effect Safe Operating Area**

LET (MeV/(mg/cm <sup>2</sup> ))	Energy (MeV)	Range (μm)	V <sub>DS</sub> (V)				
			@V <sub>GS</sub> = 0V	@V <sub>GS</sub> = -5V	@V <sub>GS</sub> = -10V	@V <sub>GS</sub> = -15V	@V <sub>GS</sub> = -20V
39 ± 5%	410 ± 5%	50 ± 5%	150	150	150	150	150
61 ± 5%	825 ± 5%	66 ± 7.5%	150	150	150	40	-
90 ± 5%	1470 ± 5%	80 ± 5%	50	50	30	-	-



**Fig a.** Typical Single Event Effect, Safe Operating Area

For footnotes refer to the last page



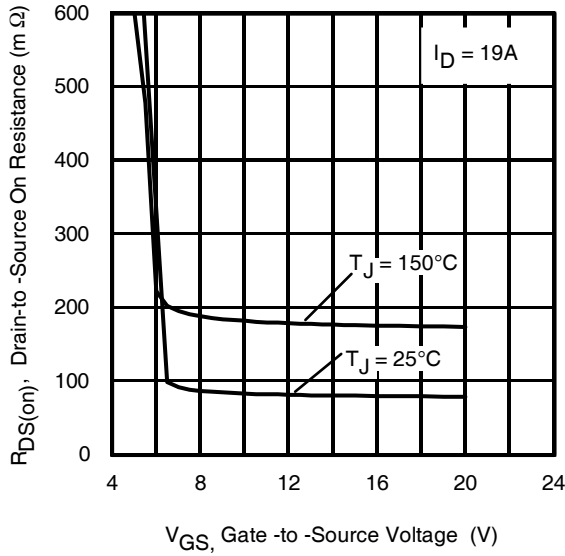


Fig 5. Typical On-Resistance Vs Gate Voltage

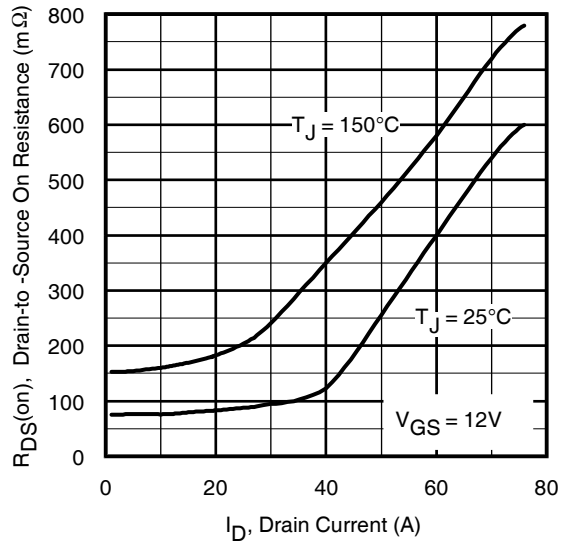


Fig 6. Typical On-Resistance Vs Drain Current

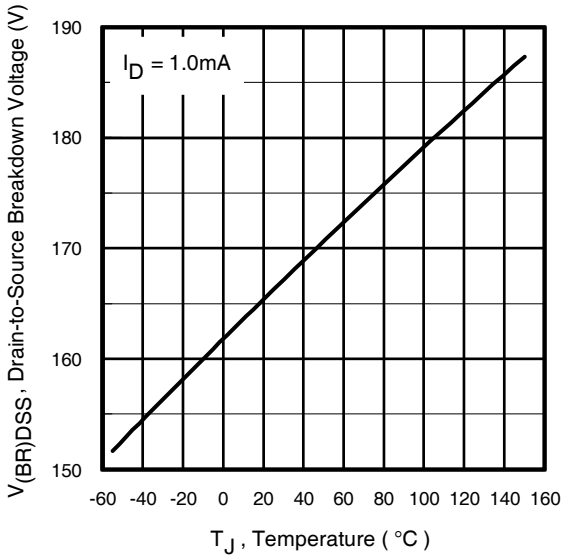


Fig 7. Typical Drain-to-Source Breakdown Voltage Vs Temperature

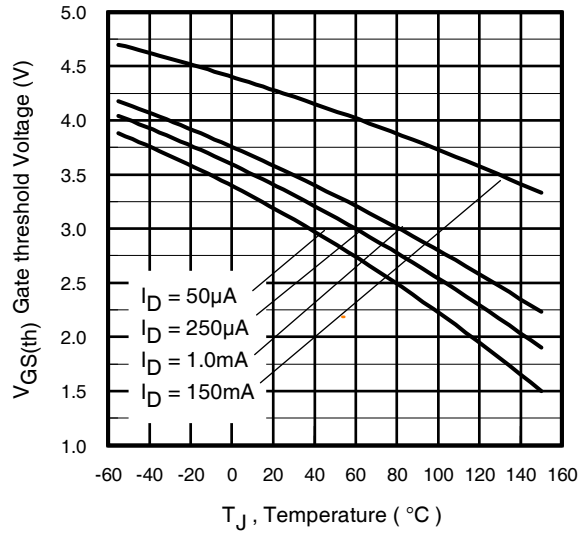
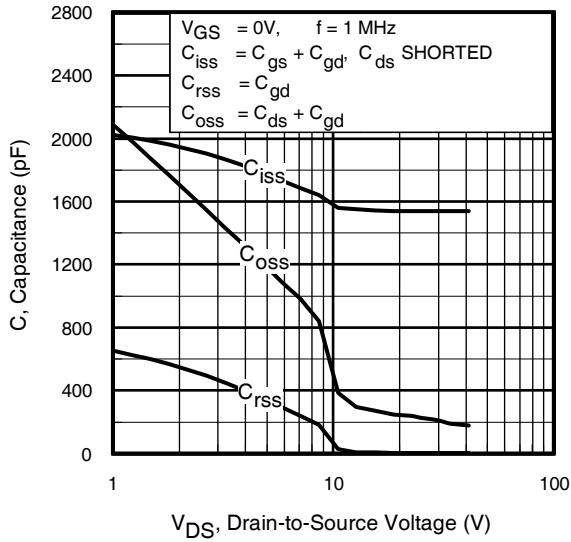
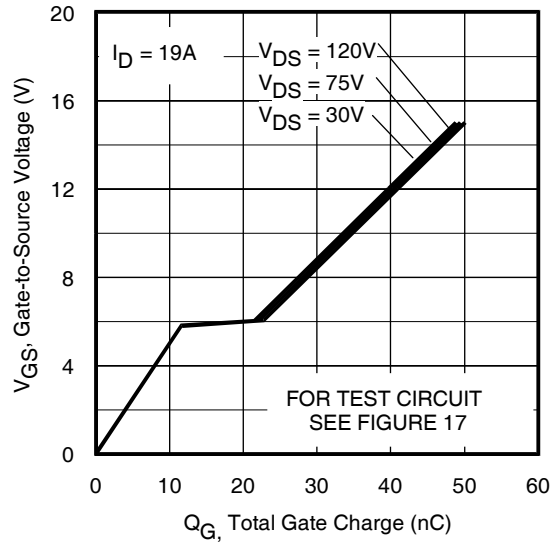


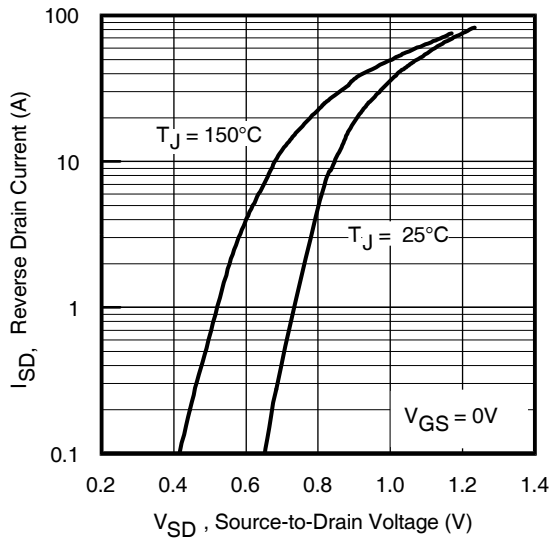
Fig 8. Typical Threshold Voltage Vs Temperature



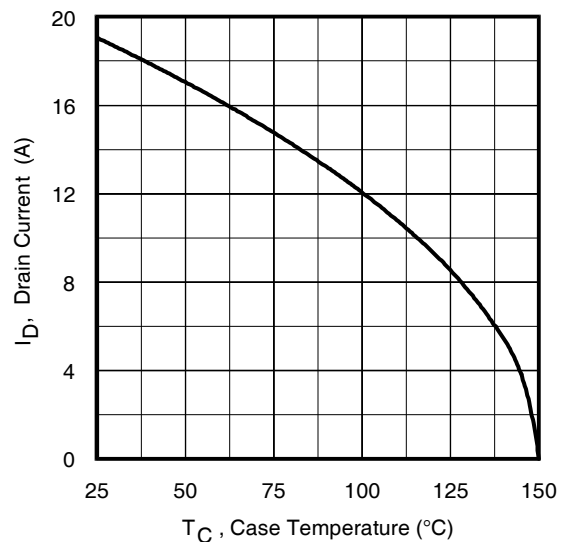
**Fig 9.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 10.** Typical Gate Charge Vs. Gate-to-Source Voltage



**Fig 11.** Typical Source-Drain Diode Forward Voltage



**Fig 12.** Maximum Drain Current Vs. Case Temperature

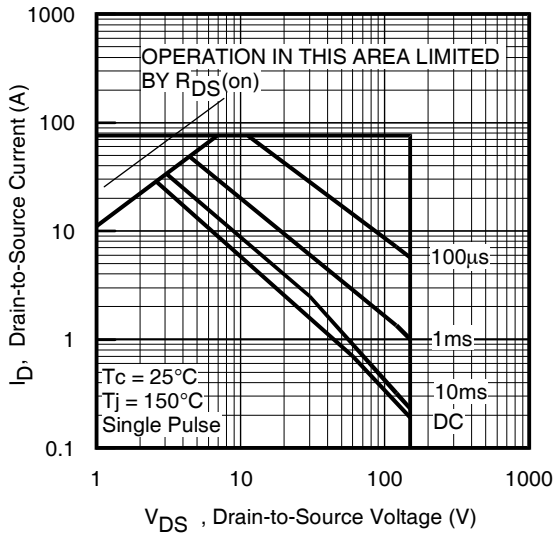


Fig 13. Maximum Safe Operating Area

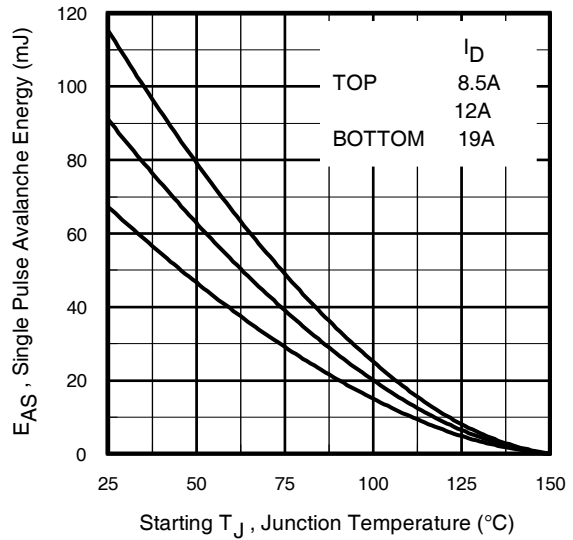


Fig 14. Maximum Avalanche Energy Vs. Drain Current

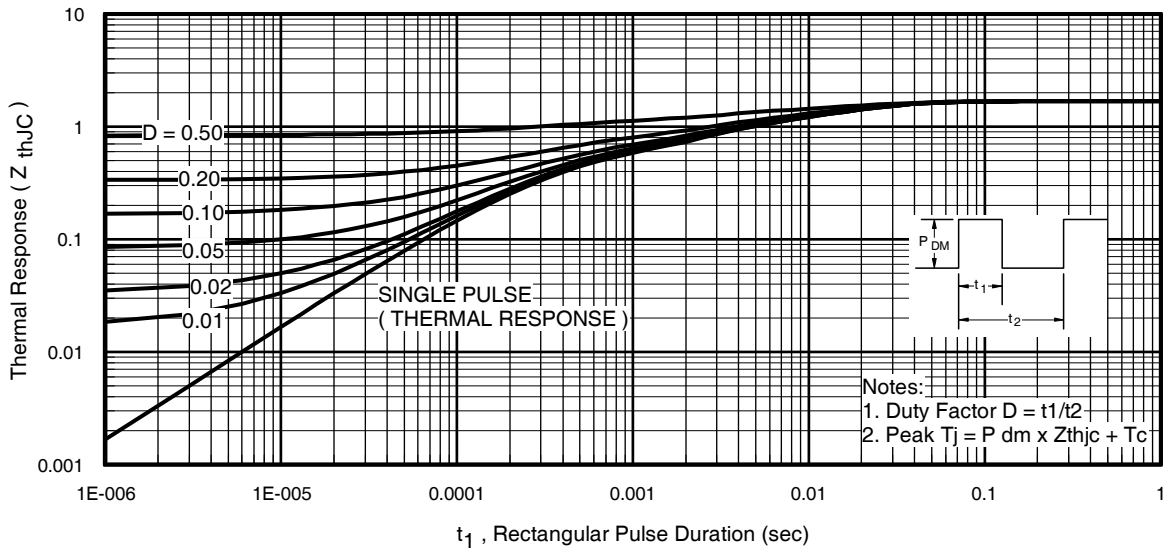
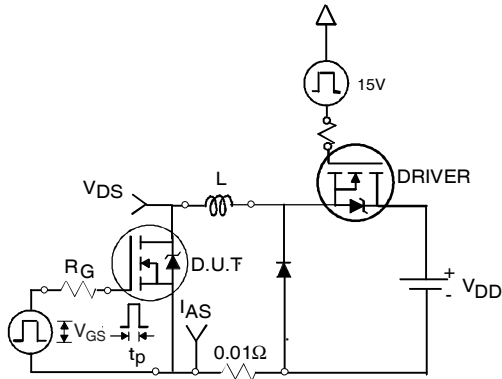


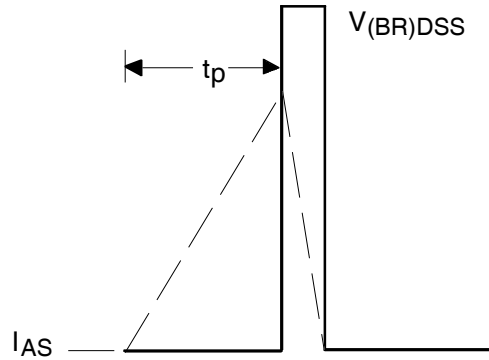
Fig 15. Maximum Effective Transient Thermal Impedance, Junction-to-Case

**IRHYB67134CM**

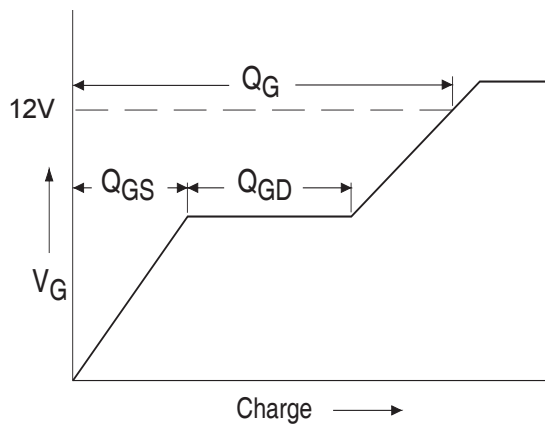
**Pre-Irradiation**



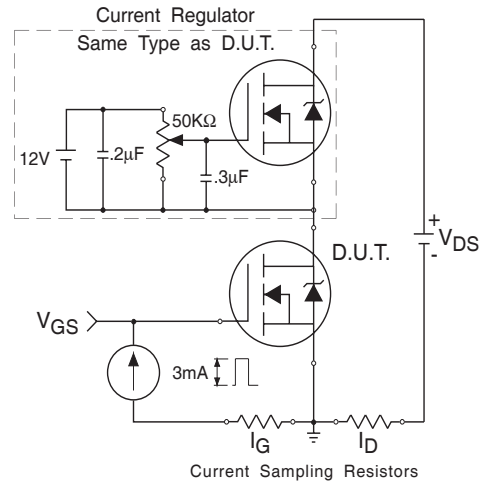
**Fig 16a.** Unclamped Inductive Test Circuit



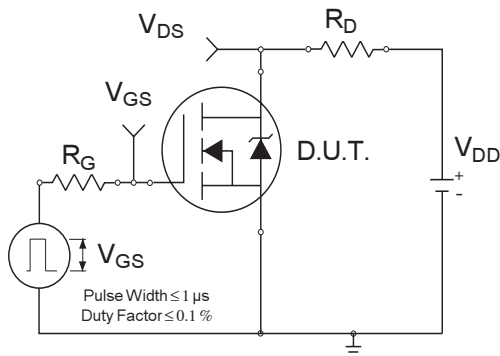
**Fig 16b.** Unclamped Inductive Waveforms



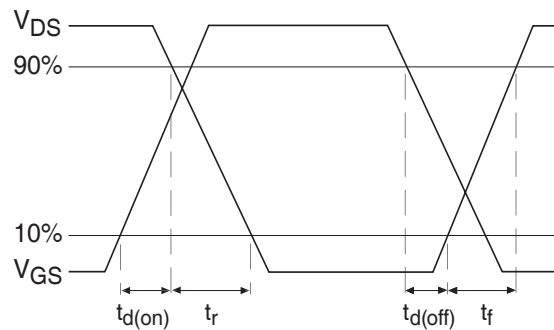
**Fig 17a.** Basic Gate Charge Waveform



**Fig 17b.** Gate Charge Test Circuit



**Fig 18a.** Switching Time Test Circuit



**Fig 18b.** Switching Time Waveforms



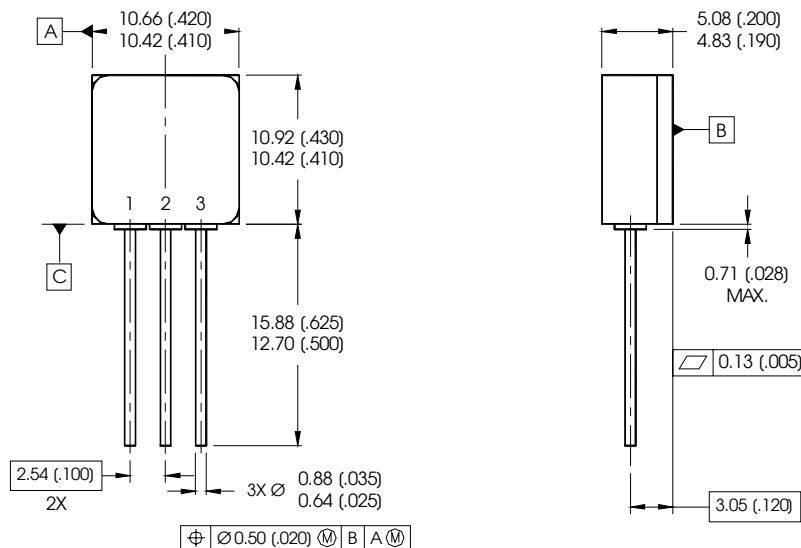
## Pre-Irradiation

IRHYB67134CM

### Footnotes:

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ②  $V_{DD} = 25V$ , starting  $T_J = 25^\circ C$ ,  $L = 0.37mH$   
Peak  $I_L = 19A$ ,  $V_{GS} = 12V$
- ③  $I_{SD} \leq 19A$ ,  $di/dt \leq 570A/\mu s$ ,  
 $V_{DD} \leq 150V$ ,  $T_J \leq 150^\circ C$
- ④ Pulse width  $\leq 300 \mu s$ ; Duty Cycle  $\leq 2\%$
- ⑤ **Total Dose Irradiation with  $V_{GS}$  Bias.**  
12 volt  $V_{GS}$  applied and  $V_{DS} = 0$  during irradiation per MIL-STD-750, method 1019, condition A.
- ⑥ **Total Dose Irradiation with  $V_{DS}$  Bias.**  
120 volt  $V_{DS}$  applied and  $V_{GS} = 0$  during irradiation per MIL-STD-750, method 1019, condition A.

## Case Outline and Dimensions — Low-Ohmic TO-257AA (Tabless)



### NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE TO-257AA.

### LEAD ASSIGNMENTS

- 1 = DRAIN
- 2 = SOURCE
- 3 = GATE

International  
**IR** Rectifier

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